Product data sheet

1. General description

WMS30N140E is a high performance logic level N-channel MOSFET in PDFN3.3X3.3 package, which utilizes advanced Trench MOSFET technology to provide low $R_{\tiny DS(on)}$ and gate charge. It is designed and qualified in a wide range of industrial and consumer applications.



2. Features and benefits

- · Advance High Cell Density Trench Technology
- Low R_{DS(on)} to Minimize Conduction Losses
- Low Capacitance to Minimize Switching Losses
- · Optimized Gate Charge to Minimize Driver Losses
- 100% UIS Tested
- · RoHS Compliant, Halogen Free and Lead Free

3. Applications

- DC-DC Converters
- BLDC Motor Control
- Load Switch
- Lithium-ion Battery Protection

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes		Values		Unit		
Absolute	Absolute maximum rating								
V _{DS}	drain-source voltage				30		V		
V _{GS}	gate-source voltage				±20		V		
I _D	continuous drain current	V _{GS} = 10 V; T _{mb} = 25 °C	[1]		30		А		
P _{tot}	power dissipation	T _{mb} = 25 °C		19 V		W			
T _j	junction temperature			-55 to 150 °C		°C			
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit		
Static cha	aracteristics								
R _{DS(on)}	drain-source on-state	V _{GS} = 10 V, I _D = 16 A		-	10	14	mΩ		
resistance		V _{GS} = 4.5 V, I _D = 5 A		-	16	21	mΩ		
Dynamic (Dynamic characteristics								
$Q_{G(tot)}$	total gate charge	I _D = 16 A; V _{DS} = 15 V; V _{GS} = 10 V		-	16	-	nC		

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1-3	S	source	8 7 6 5	D
4	G	gate		
5-8	D	drain	0 1 2 3 4	sym300 S

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number		Small packing quantity	Package version	Package issue date
WMS30N140E	PDFN3.3X3.3	WMS30N140EJ	Reel	5000	PDFN3.3X3.3N	22-Sep-2022

7. Marking

Table 4. Marking codes

Type number	Marking codes
WMS30N140E	3N140

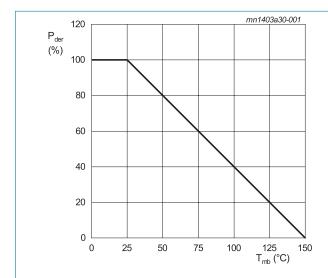
8. Limiting values

Table 5. Limiting values

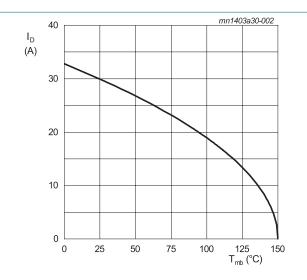
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V _{DS}	drain-source voltage			30	V
V _{GS}	gate-source voltage			±20	V
I _D	continuous drain current	V _{GS} = 10 V; T _{mb} = 25 °C	[1]	30	Α
		V _{GS} = 10 V; T _{mb} = 120 °C		15	Α
I _{DM}	pulsed drain current	t _p = 10 μs; T _{mb} = 25 °C		120	Α
P _{tot}	power dissipation	T _{mb} = 25 °C		19	W
E _{as}	single pulse drain-to- source avalanche	I_{AS} = 14 A; L = 0.1 mH; R_{GS} = 25 Ω ; V_{GS} = 10 V; T_{J} = 25 °C		9.8	mJ
T _{stg}	storage temperature			-55 to 150	°C
T _j	junction temperature			-55 to 150	°C

[1] Calculated continuous current based on maximum allowable junction temperature. Package current limitation is 16A.



P_{der} = (P_{tot} / P_{tot(25 °C)}) x 100% Fig. 1. Normalized total power dissipation as a function of mounting base temperature



V_{GS} = 10 V
Fig. 2. Continuous Drain Current as a function of mounting base temperature

9. Thermal & Mechanical characteristics

Table 6. Thermal & Mechanical characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base			-	5.0	6.5	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	[2]	-	-	60	K/W

[2] Surface mount on FR4 board of 1 inch², 1 oz copper.

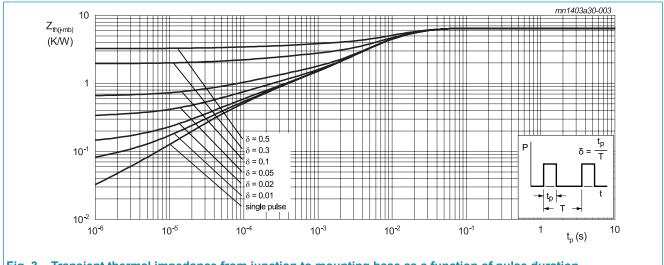


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

T_i = 25 °C unless otherwise noted

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static cha	aracteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V		30	-	-	V
$V_{\text{GS(th)}}$	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}$		1.0	1.5	2.4	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}$		-	-	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$		-	-	10	μA
I _{GSS}	gate leakage current	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$		-	-	±100	nA
R _{DS(on)}	drain-source on-state	V _{GS} = 10 V; I _D = 16 A		-	10	14	mΩ
	resistance	$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A}$		-	16	21	mΩ
R_G	gate resistance	f = 1 MHz		-	3	-	Ω
Dynamic	characteristics						
Q _{G(tot)}	total gate charge	I _D = 16 A; V _{DS} = 15 V; V _{GS} = 10 V		-	16	-	nC
Q _{GS}	gate-source charge			-	2.9	-	nC
Q_{GD}	gate-drain charge			-	3.3	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz		-	832	-	pF
C _{oss}	output capacitance			-	105	-	pF
C _{rss}	reverse transfer capacitance			-	84	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V}; R_G = 6 \Omega;$		-	3.4	-	ns
t _r	rise time	$I_D = 16 A$		-	6.7	-	ns
$t_{\text{d(off)}}$	turn-off delay time			-	10	-	ns
t _f	fall time			-	3.3	-	ns
Source-d	rain diode		-				
V _{SD}	source-drain voltage	V _{GS} = 0 V; I _S = 1 A		-	0.74	1	V
		V _{GS} = 0 V; I _S = 1 A; T _j = 125 °C		-	0.59	-	V
Is	body-diode continuous current	T _{mb} = 25 °C		-	-	21	А
t _{rr}	reverse recovery time	$V_{GS} = 0 \text{ V}; I_S = 16 \text{ A}; \text{ di/dt} = 100 \text{ A/}\mu\text{s}$		-	13	-	ns
Q _{rr}	reverse recovered charge			-	3.8	-	nC
I _{rrm}	reverse recovery current			-	0.7	-	Α

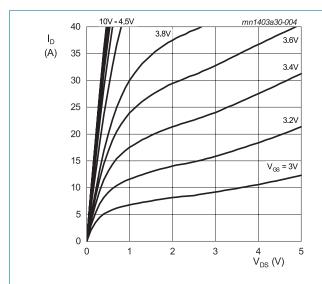
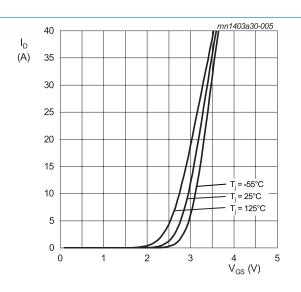
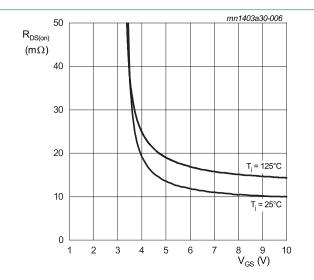


Fig. 4. Drain current as a function of drain-source voltage; typical values



V_{DS} = 5 V

Fig. 5. Drain current as a function of gate-source voltage; typical values



I_D = 16 A

Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

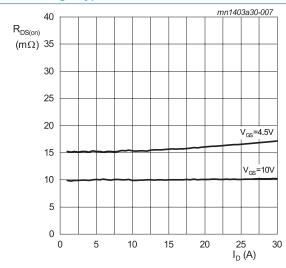
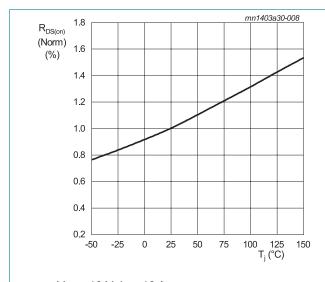
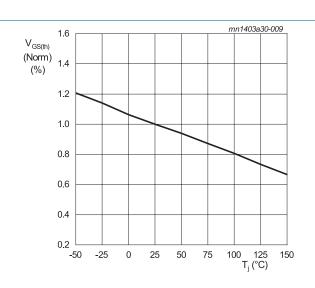


Fig. 7. Drain-source on-state resistance as a function of drain current; typical values



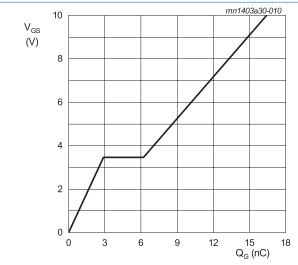
 V_{GS} = 10 V; I_{D} = 16 A

Fig. 8. Normalized drain-source on-state resistance as a function of junction temperature



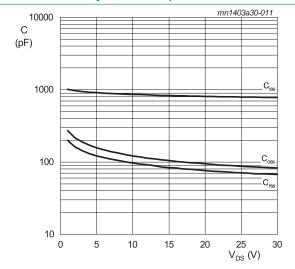
 V_{DS} = V_{GS} ; I_D = 250 μA

Fig. 9. Normalized gate-source threshold voltage as a function of junction temperature



 $I_D = 16 \text{ A}; V_{DS} = 15 \text{ V}$

Fig. 10. Gate-source voltage as a function of gate charge; typical values

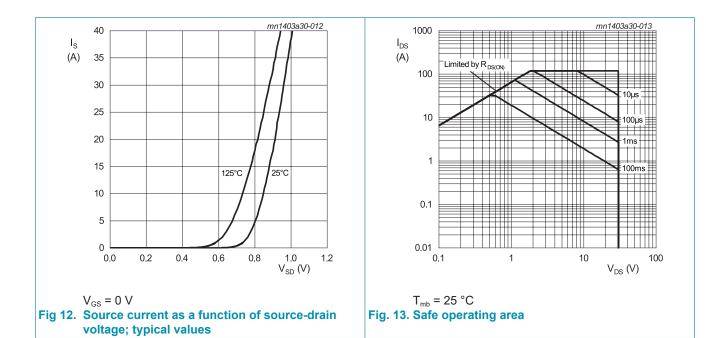


 $V_{GS} = 0 V; f = 1 MHz$

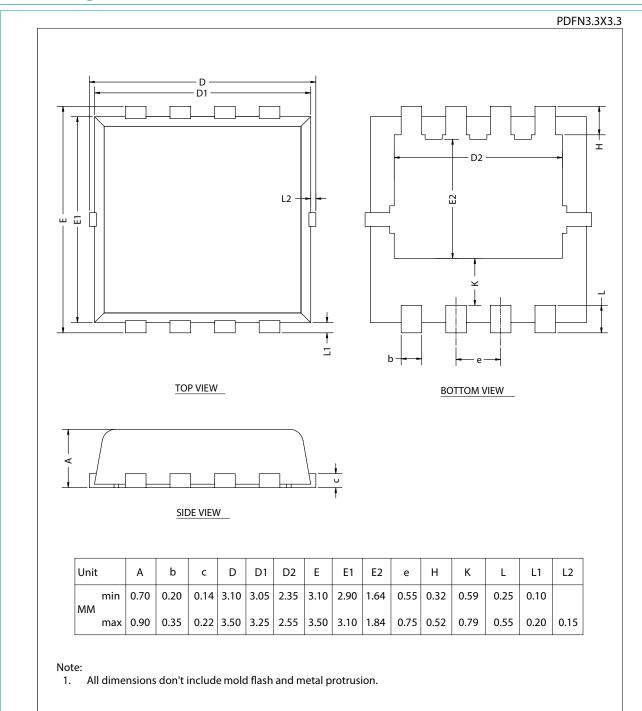
Fig 11. Capacitances as a function of drain-source voltage; typical values

WeEn Semiconductors

N-Channel Silicon MOSFET



11. Package outline



12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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